

General Description

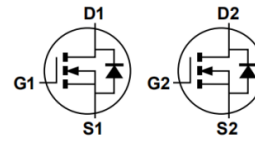
It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

Features

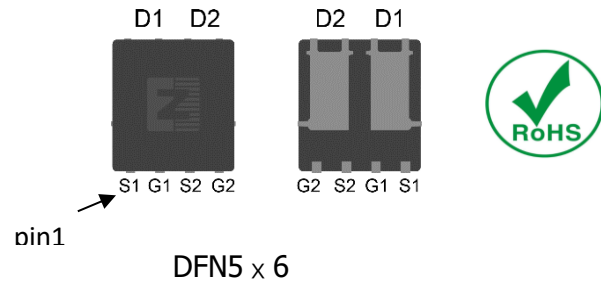
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Dual DIE in one package

Application

- Battery Powered Systems
- BLDC Motor driver
- Load Switch
- DC-DC

Product Summary


$V_{DS1} = 60V$
 $V_{DS2} = 60V$
 $R_{DS(ON)1} = 28m\Omega$
 $R_{DS(ON)2} = 28m\Omega$
 $I_{D1} = 20A$
 $I_{D2} = 20A$


Ordering Information:

Part NO.	ZMD68602N
Marking	ZMD68602
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

Absolute Maximum Ratings ($T_c = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	20	A
	$I_D @ T_C = 75^\circ C$	15.2	A
	$I_D @ T_C = 100^\circ C$	12.6	A
Pulsed Drain Current ^①	I_{DM}	60	A
Total Power Dissipation	$P_D @ T_C = 25^\circ C$	62.5	W
Total Power Dissipation ^②	$P_D @ T_A = 25^\circ C$	2.0	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	25	mJ
ESD Level (HBM)		CLASS 1C	

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	60	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	260	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2	1.8	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 12A$		28	36	m Ω
		$V_{GS} = 4.5V, I_D = 6A$		34	42	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 10A$		5		S
Source-drain voltage	V_{SD}	$I_S = 12A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V$ $f = 1MHz$	-	1300	-	pF
Output capacitance	C_{oss}		-	53	-	
Reverse transfer capacitance	C_{rss}		-	31	-	

•Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$ $I_D = 5A$ $V_{GS} = 10V$	-	17	-	nC
Gate - Source charge	Q_{gs}		-	4.1	-	
Gate - Drain charge	Q_{gd}		-	2.5	-	

Fig.1 Power Dissipation

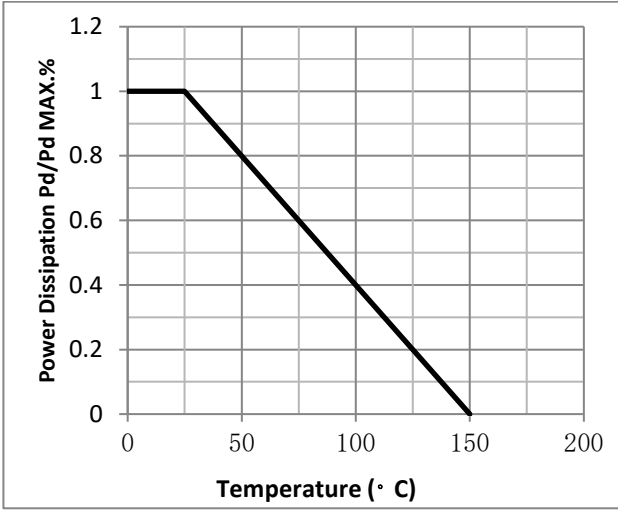


Fig.2 Typical output Characteristics

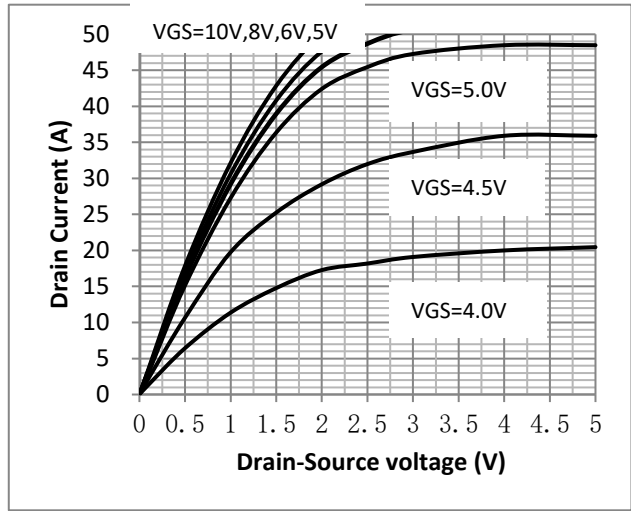


Fig.3 Threshold Voltage V_{GS(th)} V.S Junction Temperature

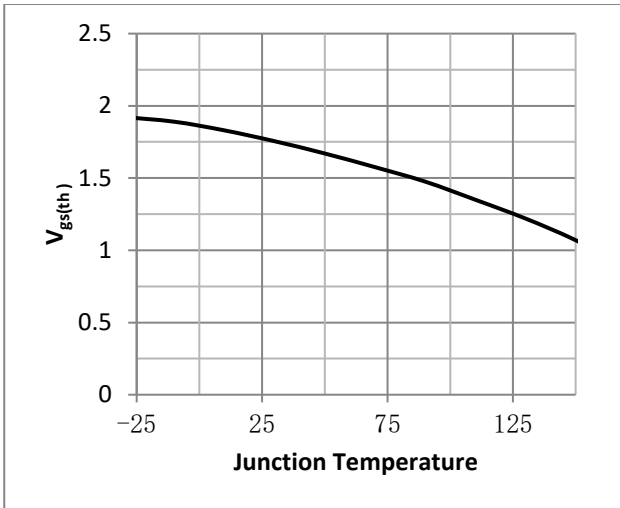


Fig.4 Resistance V.S Drain Current

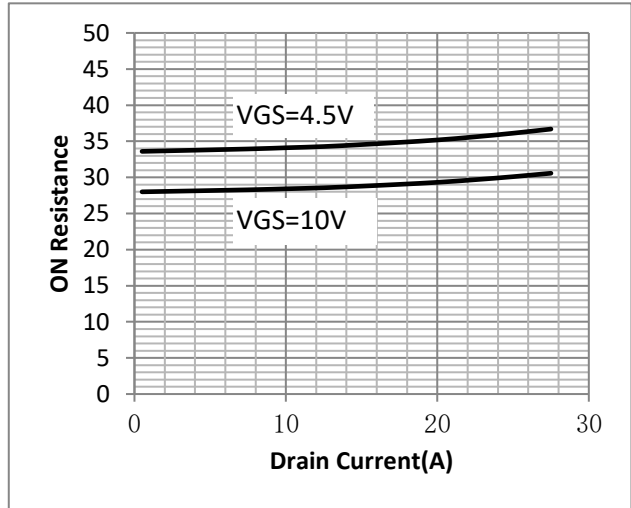


Fig.5 On-Resistance VS Gate Source Voltage

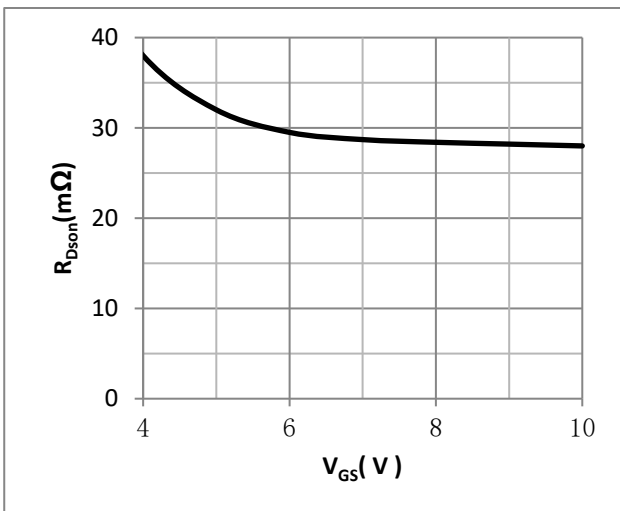


Fig.6 On-Resistance V.S Junction Temperature

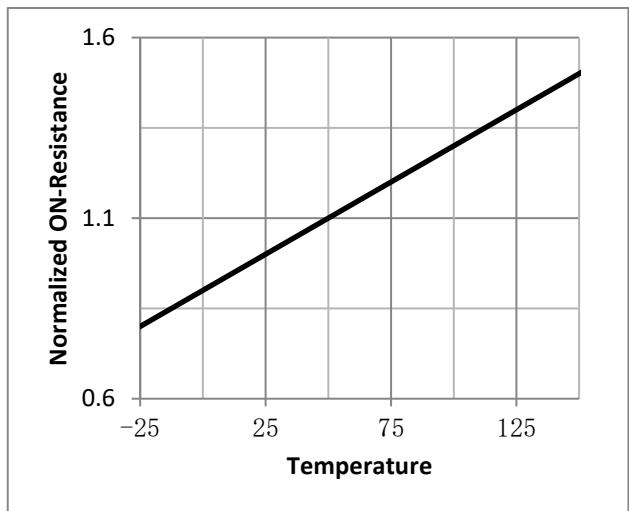


Fig.7 SOA Maximum Safe Operating Area

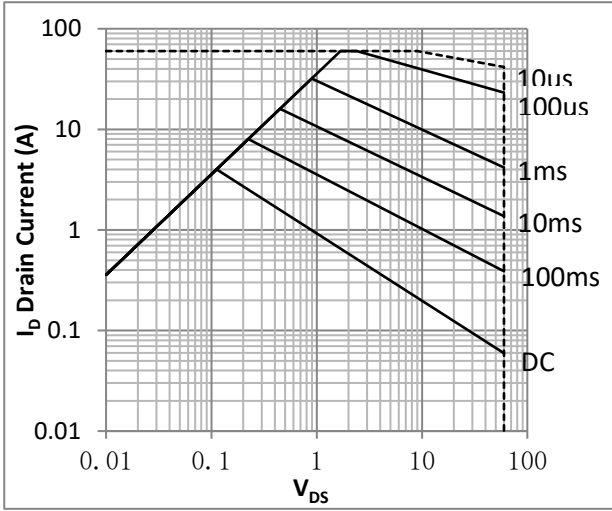


Fig.8 ID-Junction Temperature

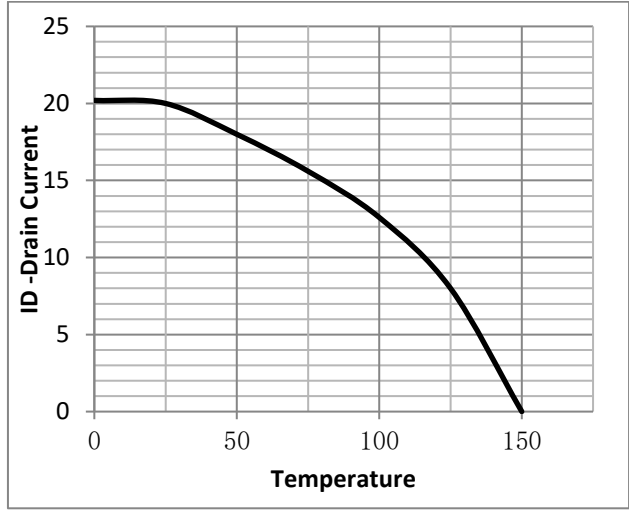


Fig.9 Gate-Charge Characteristics

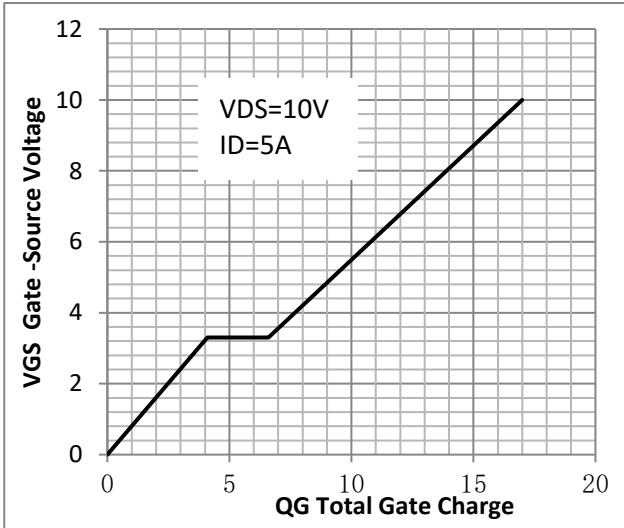


Fig.10 Capacitance Characteristics

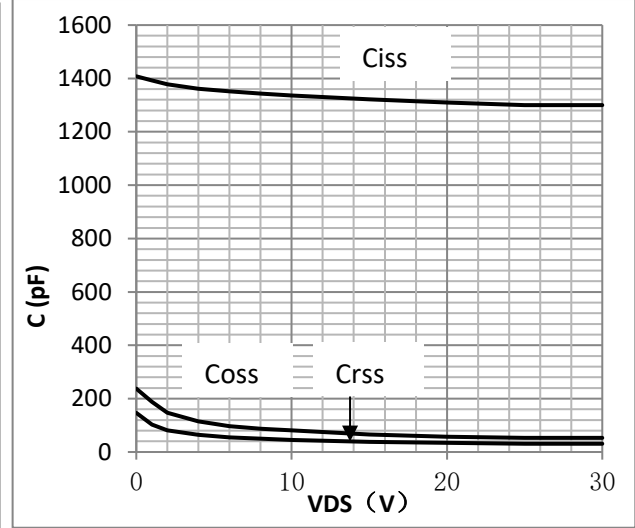


Fig.11 Transfer Characteristics

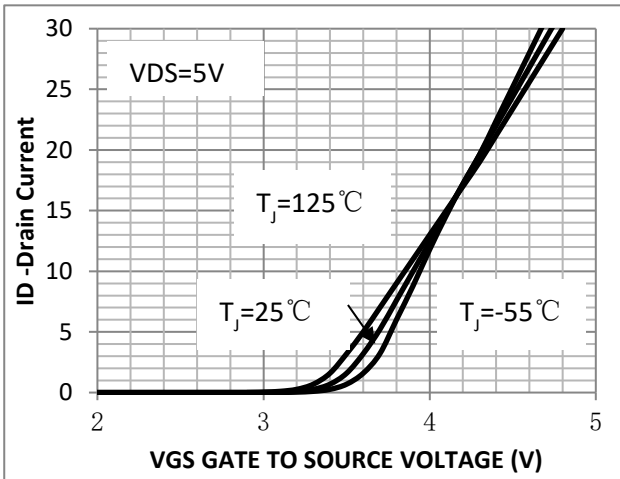


Fig.12 Gate Charge Measurement Circuit

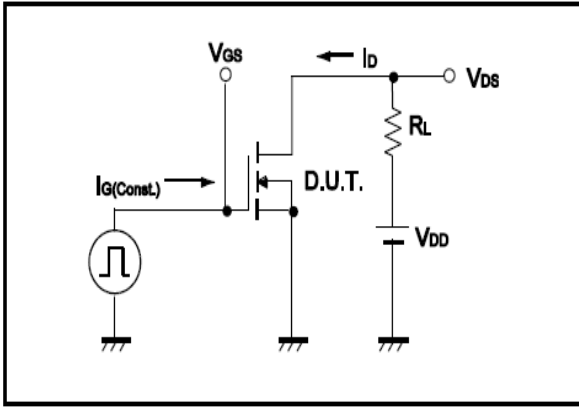


Fig.13 Gate Charge Waveform

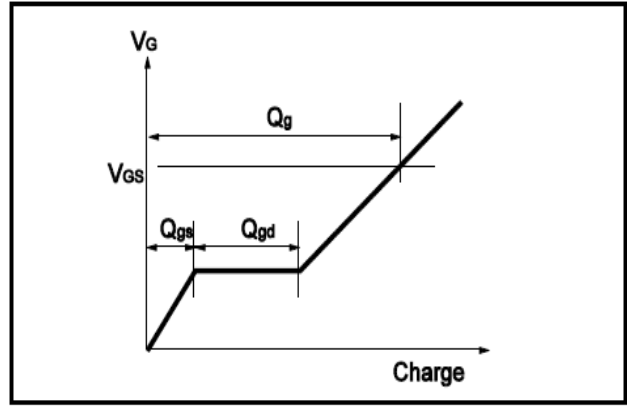


Fig.14 Switching Time Measurement Circuit

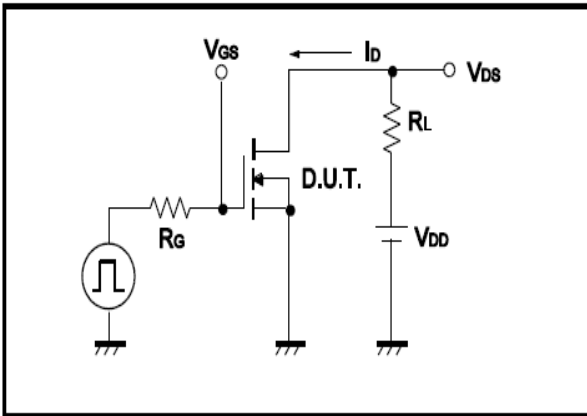


Fig.15 Switching Time Waveform

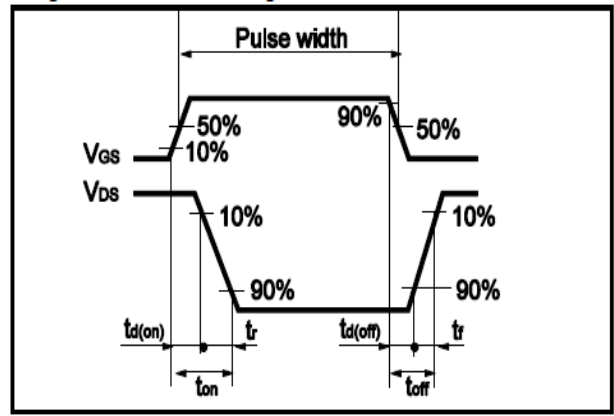


Fig.16 Avalanche Measurement Circuit

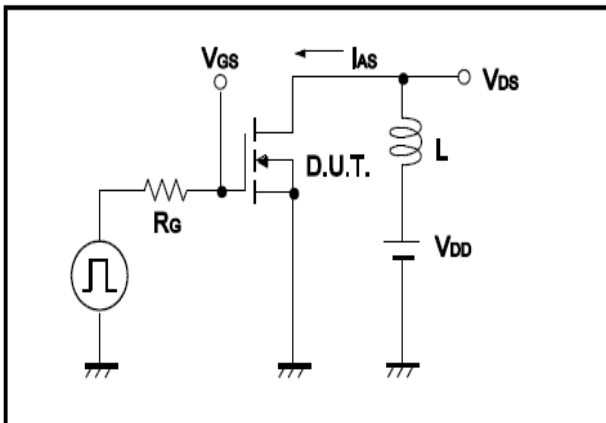
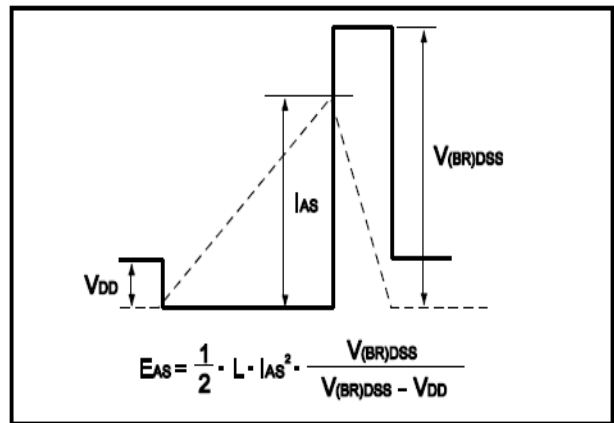


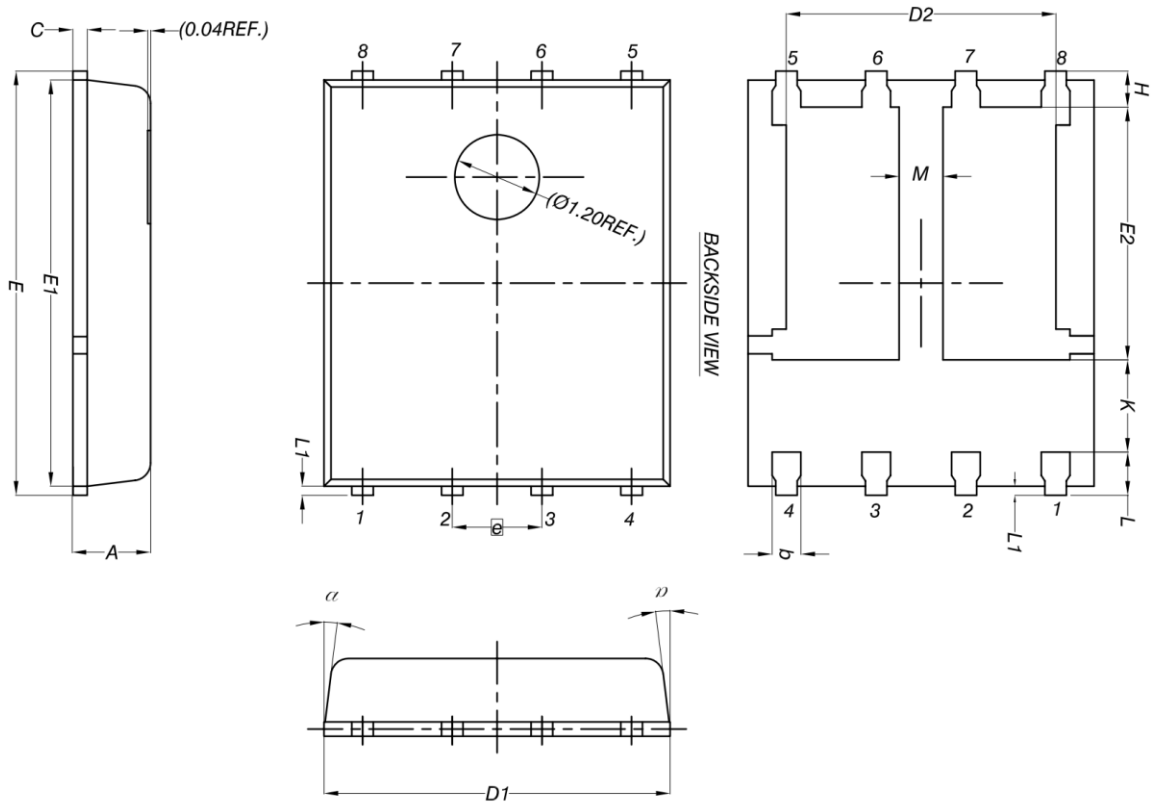
Fig.17 Avalanche Waveform



Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

•Dimensions (DFN5x6)



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
M	0.50	-	-
α	0°	-	12°

